

Band switching diode

1SS356

●Applications

High frequency switching

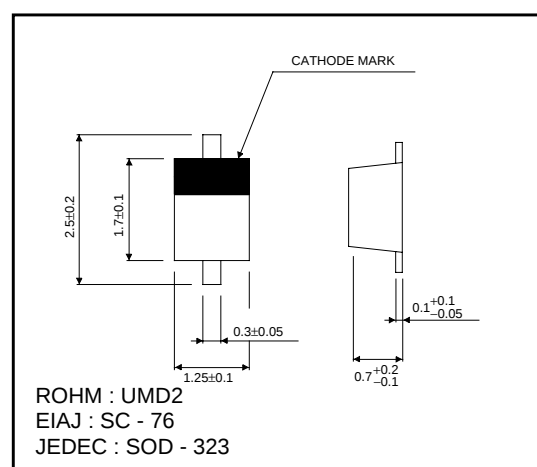
●Features

- 1) Small surface mounting type. (UMD2)
- 2) High reliability.

●Construction

Silicon epitaxial planar

●External dimensions (Units : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
DC reverse voltage	V_R	35	V
DC forward current	I_F	100	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55~+125	°C

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	—	1.0	V	$I_F=10\text{mA}$
Reverse current	I_R	—	—	10	nA	$V_R=25\text{V}$
Capacitance between terminals	C_T	—	—	1.2	pF	$V_R=6\text{V}$, $f=1\text{MHz}$
Forward operating resistance	r_F	—	—	0.9	Ω	$I_F=2\text{mA}$, $f=100\text{MHz}$

Diodes

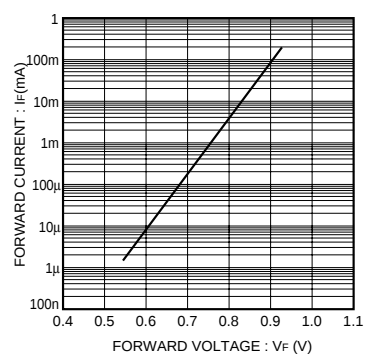
●Electrical characteristic curves ($T_a=25^\circ\text{C}$)

Fig. 1 Forward characteristics

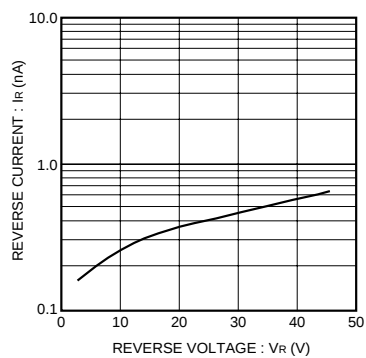


Fig. 2 Reverse characteristics

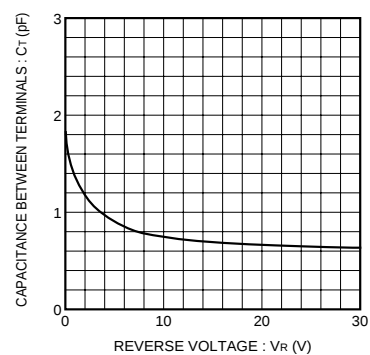


Fig. 3 Capacitance between terminals characteristics

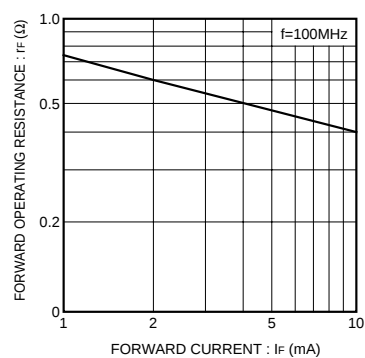


Fig. 4 Forward operating resistance characteristics